

TO-92 Plastic-Encapsulate Transistors

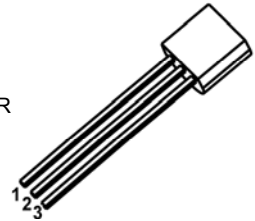
2SA1980 TRANSISTOR (PNP)

FEATURES

- Low Collector Saturation Voltage: $V_{CE(sat)} = -0.3V(\text{Max.})$
- Low Output Capacitance : $C_{ob} = 4pF$ (Typ.)
- Complementary Pair with 2SC5343

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Power Dissipation	625	mW
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -2\text{mA}$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		4	7	pF
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}, f = 1\text{KHz}, R_S = 10\text{K}\Omega$			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	G	L
Range	70-140	120-240	200-400	300-700